

DATASHEET

Sidelooker Phototransistor PT908-7B-F



Features

- Fast response time
- High sensitivity
- Small junction capacitance
- Pb Free
- This product itself will remain within RoHS compliant version

Descriptions

- PT908-7B-F is a phototransistor in miniature package which is molded in a black plastic with spherical top view lens
- The device is spectrally matched to infrared emitting diode
- Compliance with EU REACH
- Compliance Halogen Free (Br<900ppm, Cl<900ppm, Br+ Cl<1500ppm)

Applications

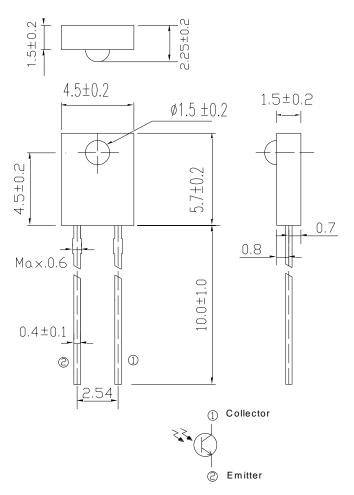
- Optoelectronic switch
- VCR, Video Camera
- Floppy disk drive
- Infrared applied system

Device Selection Guide

Part Category	Chip Material	Lens Color
PT	Silicon	Black



Package Dimensions



Notes: 1. All dimensions are in millimeters

2. Tolerances unless dimensions ±0.3 mm

Absolute Maximum Ratings (Ta=25°C)

1500 ato maximum ratingo (14-20 0)						
Parameter	Symbol	Rating	Units			
Collector-Emitter Voltage	V_{CEO}	30	V			
Emitter-Collector-Voltage	V_{ECO}	5	V			
Collector Current	I _C	20	mA			
Operating Temperature	T_{opr}	-25 ~ +85	$^{\circ}\!\mathbb{C}$			
Storage Temperature	T_{stg}	-40 ~ +85	$^{\circ}\!\mathbb{C}$			
Soldering Temperature *1	T _{sol}	260	$^{\circ}\! \mathbb{C}$			
Power Dissipation at (or below) 25°C Free Air Temperature	P _d	75	mW			

Notes: *1. Soldering time ≤ 5 second

Electro-Optical Characteristics (Ta=25°C)

Parameter	Symbol	Condition	Min.	Тур.	Max.	Units
i arameter	Syllibol	Condition	IAIIII.	Typ.	IVIAA.	Ullita
Rang of Spectral Bandwidth	λ _{0.5}		740		1100	nm
Wavelength of Peak Sensitivity	λр			940		nm
Collector-Emitter Breakdown Voltage	BV _{CEO}	I _C =100μA Ee=0mW/cm ²	30			V
Emitter-Collector Breakdown Voltage	BV _{ECO}	I _E =100μA Ee=0mW/cm ²	5			V
Collector Dark Current	I _{CEO}	V _{CE} =20V Ee=0mW/cm ²			100	μΑ
Collector-Emitter Saturation Voltage	V _{CE(sat)}	I _C =2mA Ee=1mW/cm ²			0.4	V
On State Collector Current	I _{C(on)}	V _{CE} =5V Ee=0.555mW/cm ²	0.80		3.06	mA

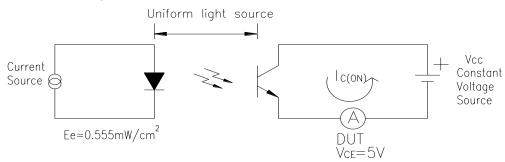
Symbol	condition	Ranks	Min	Max	Unit
I _{C(ON)}		BIN1	0.80	1.53	
	V _{CE} =5V Ee=0.555mW/cm ²	BIN2	1.11	1.98	0
		BIN3	1.43	2.68	mA
		BIN4	1.59	3.06	

Notes: This bin table is only for reference, not for specific bin shipment.

Test Method For $I_{C(ON)}$:

Condition: V_{CE}=5V Ee=0.555mW/cm²

Light current test method for PT:



Typical Electro-Optical Characteristics Curves

Fig.1 Spectral Sensitivity

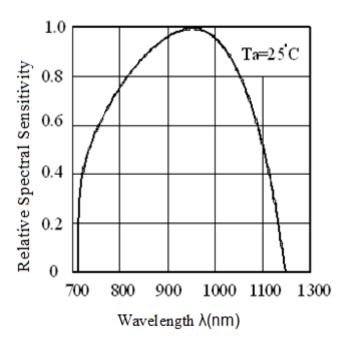


Fig.2 Collector Current vs.

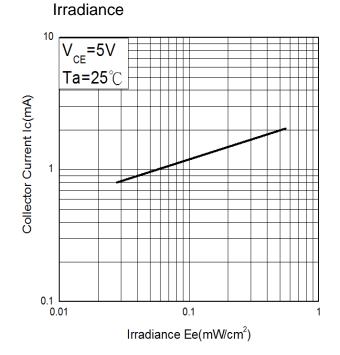
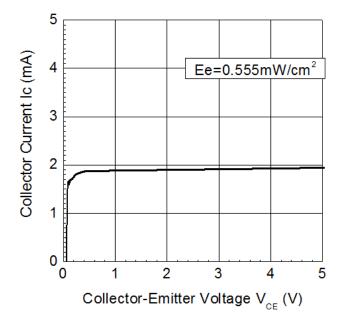


Fig.3 Collector Current vs.

Collector-Emitter Voltage

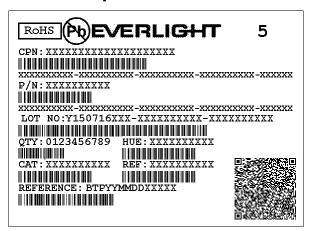




Packing Quantity Specification

1000 pcs/bag,10 bags/box 10 boxes/carton

Label Form Specification



CPN: Customer Part Number

• P/N: Part Number

QTY: Packing Quantity

· CAT: Ranks

REF: Reference

· LOT No: Lot Number

Application Restrictions

- 1. Above specification may be changed without notice. EVERLIGHT will reserve authority on material change for above specification.
- 2. The graphs shown in this datasheet are representing typical data only and do not show guaranteed values.
- 3. When using this product, please observe the absolute maximum ratings and the instructions for use outlined in these specification sheets. EVERLIGHT assumes no responsibility for any damage resulting from use of the product which does not comply with the absolute maximum ratings and the instructions included in these specification sheets.
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